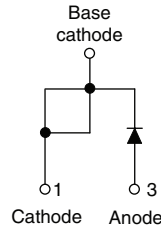


## Input Rectifier Diode TO-220 FULL-PAK, 10 A




TO-220AC FULL-PAK



### DESCRIPTION

The 10ETS..FP rectifier series has been optimized for very low forward voltage drop, with moderate leakage. The glass passivation technology used has reliable operation up to 150 °C junction temperature.

Typical applications are in input rectification and these products are designed to be used with Vishay HPP switches and output rectifiers which are available in identical package outlines.

Fully isolated package ( $V_{INS} = 2500 V_{RMS}$ ) is UL E78996 approved 

This product has been designed and qualified for industrial level.

### PRODUCT SUMMARY

$V_F$ at 10 A	< 1.1 V
$I_{FSM}$	200 A
$V_{RRM}$	800/1200 V

### OUTPUT CURRENT IN TYPICAL APPLICATIONS

APPLICATIONS	SINGLE-PHASE BRIDGE	THREE-PHASE BRIDGE	UNITS
Capacitive input filter $T_A = 55\text{ °C}$ , $T_J = 125\text{ °C}$ common heatsink of 1 °C/W	12.0	16.0	A

### MAJOR RATINGS AND CHARACTERISTICS

SYMBOL	CHARACTERISTICS	VALUES	UNITS
$I_{F(AV)}$	Sinusoidal waveform	10	A
$V_{RRM}$	Range	800/1200	V
$I_{FSM}$		200	A
$V_F$	10 A, $T_J = 25\text{ °C}$	1.1	V
$T_J$		- 40 to 150	°C

### VOLTAGE RATINGS

PART NUMBER	$V_{RRM}$ , MAXIMUM PEAK REVERSE VOLTAGE V	$V_{RSM}$ , MAXIMUM NON-REPETITIVE PEAK REVERSE VOLTAGE V	$I_{RRM}$ AT 150 °C mA
10ETS08FP	800	900	0.5
10ETS12FP	1200	1300	

### ABSOLUTE MAXIMUM RATINGS

PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS
Maximum average forward current	$I_{F(AV)}$	$T_C = 105\text{ °C}$ , 180° conduction half sine wave	10	A
Maximum peak one cycle non-repetitive surge current	$I_{FSM}$	10 ms sine pulse, rated $V_{RRM}$ applied	170	
		10 ms sine pulse, no voltage reapplied	200	
Maximum $I^2t$ for fusing	$I^2t$	10 ms sine pulse, rated $V_{RRM}$ applied	130	A <sup>2</sup> s
		10 ms sine pulse, no voltage reapplied	145	
Maximum $I^2\sqrt{t}$ for fusing	$I^2\sqrt{t}$	t = 0.1 to 10 ms, no voltage reapplied	1450	A <sup>2</sup> √s

# 10ETS..FP High Voltage Series



Vishay High Power Products

Input Rectifier Diode  
TO-220 FULL-PAK, 10 A

ELECTRICAL SPECIFICATIONS					
PARAMETER	SYMBOL	TEST CONDITIONS		VALUES	UNITS
Maximum forward voltage drop	$V_{FM}$	10 A, $T_J = 25\text{ }^\circ\text{C}$		1.1	V
Forward slope resistance	$r_t$	$T_J = 150\text{ }^\circ\text{C}$		20	$\text{m}\Omega$
Threshold voltage	$V_{F(TO)}$			0.82	V
Maximum reverse leakage current	$I_{RM}$	$T_J = 25\text{ }^\circ\text{C}$	$V_R = \text{Rated } V_{RRM}$	0.05	mA
		$T_J = 150\text{ }^\circ\text{C}$		0.50	

THERMAL - MECHANICAL SPECIFICATIONS					
PARAMETER	SYMBOL	TEST CONDITIONS		VALUES	UNITS
Maximum junction and storage temperature range	$T_J, T_{Stg}$			- 40 to 150	$^\circ\text{C}$
Maximum thermal resistance, junction to case	$R_{thJC}$	DC operation		2.5	$^\circ\text{C/W}$
Maximum thermal resistance, junction to ambient	$R_{thJA}$			62	
Typical thermal resistance, case to heatsink	$R_{thCS}$	Mounting surface, smooth and greased		0.5	
Approximate weight				2	g
				0.07	oz.
Mounting torque	minimum			6 (5)	kgf · cm (lbf · in)
	maximum			12 (10)	
Marking device		Case style TO-220 FULL-PAK (94/V0)	10ETS08FP		
			10ETS12FP		



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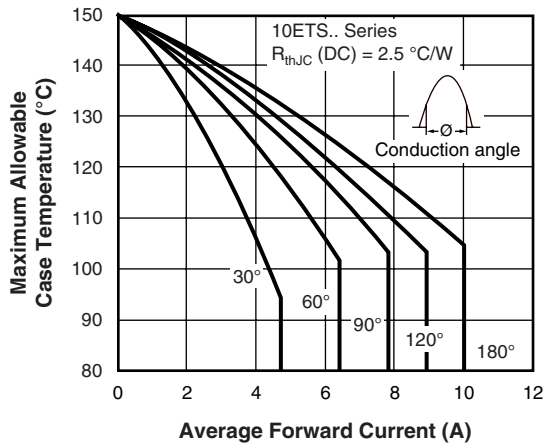


Fig. 1 - Current Rating Characteristics

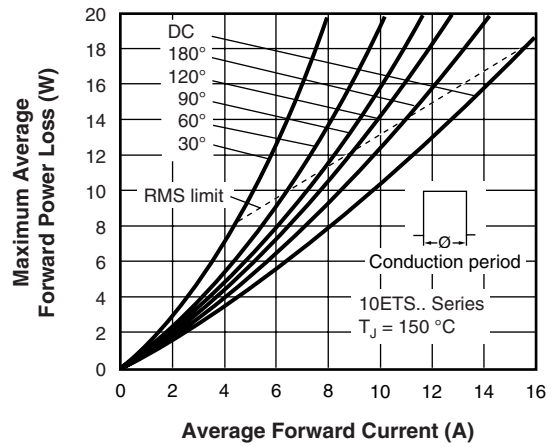


Fig. 4 - Forward Power Loss Characteristics

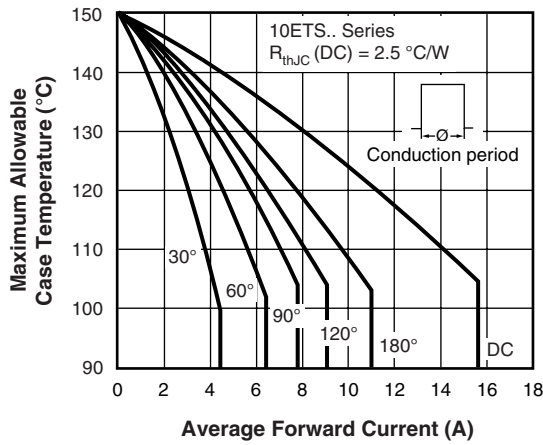


Fig. 2 - Current Rating Characteristics

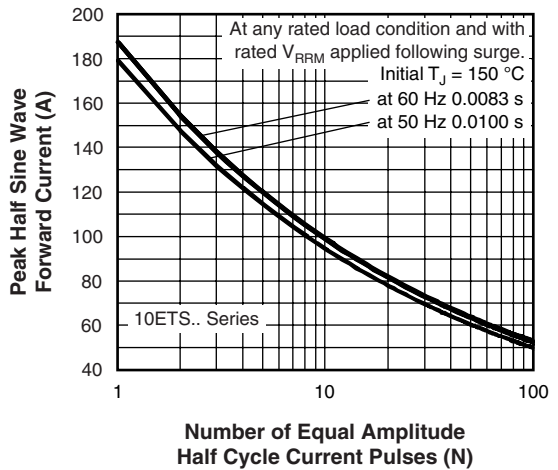


Fig. 5 - Maximum Non-Repetitive Surge Current

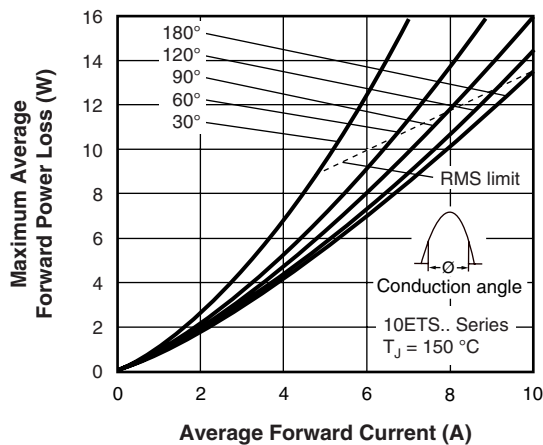


Fig. 3 - Forward Power Loss Characteristics

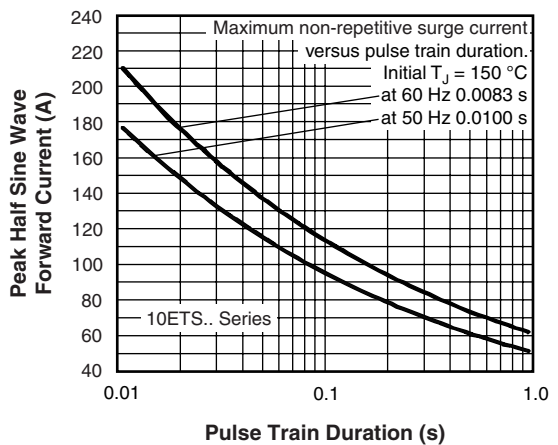


Fig. 6 - Maximum Non-Repetitive Surge Current

# 10ETS..FP High Voltage Series



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TO-220 FULL-PAK, 10 A

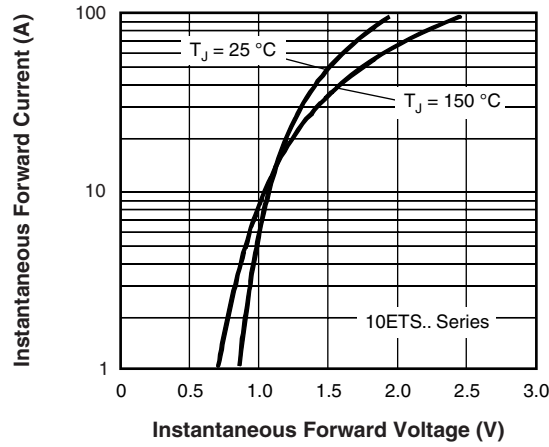


Fig. 7 - Forward Voltage Drop Characteristics

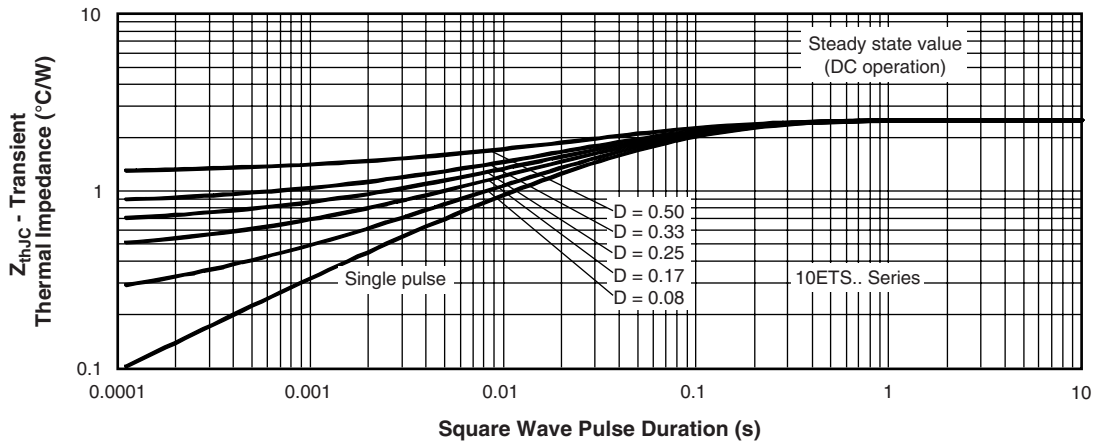


Fig. 8 - Thermal Impedance  $Z_{thJC}$  Characteristics

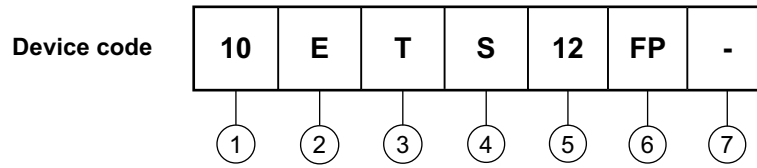


# 10ETS..FP High Voltage Series

Input Rectifier Diode  
TO-220 FULL-PAK, 10 A

Vishay High Power Products

## ORDERING INFORMATION TABLE



- 1** - Current rating (10 = 10 A)
- 2** - Circuit configuration:  
E = Single diode
- 3** - Package:  
T = TO-220AC
- 4** - Type of silicon:  
S = Standard recovery rectifier
- 5** - Voltage rating ————— 

08 = 800 V
12 = 1200 V
- 6** - FULL-PAK
- 7** -
  - None = Standard production
  - PbF = Lead (Pb)-free

LINKS TO RELATED DOCUMENTS	
Dimensions	<a href="http://www.vishay.com/doc?95005">http://www.vishay.com/doc?95005</a>
Part marking information	<a href="http://www.vishay.com/doc?95009">http://www.vishay.com/doc?95009</a>



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